

# 2N5400



# **PNP General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring high voltages.

#### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	120	V
V <sub>CBO</sub>	Collector-Base Voltage	130	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	600	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N5400	
$P_D$	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# PNP General Purpose Amplifier (continued)

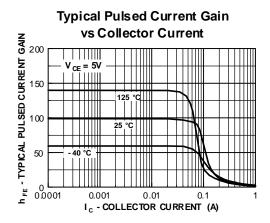
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	ARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	120		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100  \mu A, I_E = 0$	130		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10  \mu A,  I_C = 0$	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100 V, I <sub>F</sub> = 0		100	nA
050		V <sub>CB</sub> = 100 V, I <sub>E</sub> = 0, T <sub>A</sub> = 100 °C		100	μΑ
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		50	nA
		$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 50 \text{ mA}$	40 40	180	
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	30		
			40		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.2	V
V <sub>CE(sat)</sub>		I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA I <sub>C</sub> = 50 mA, I <sub>B</sub> = 5.0 mA		0.5	V
. ,	Collector-Emitter Saturation Voltage  Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.5	V
. ,		I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA I <sub>C</sub> = 50 mA, I <sub>B</sub> = 5.0 mA		0.5	V
. ,		$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.5	V
V <sub>BE(sat)</sub>		$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.5	V
V <sub>BE(Sat)</sub> SMALL S C <sub>ob</sub>	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	100	0.5 1.0 1.0	V V V
V <sub>BE(Sat)</sub> SMALL S C <sub>ob</sub>	Base-Emitter Saturation Voltage  SIGNAL CHARACTERISTICS  Output Capacitance  Current Gain - Bandwidth Product	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 10 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 100 \text{ MHz} \end{split}$		0.5 1.0 1.0 6.0 400	V V V
V <sub>BE(Sat)</sub> SMALL S  C <sub>ob</sub> f <sub>T</sub>	Base-Emitter Saturation Voltage  SIGNAL CHARACTERISTICS  Output Capacitance	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 10 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ \end{split}$	100	0.5 1.0 1.0	V V V
V <sub>BE(sat)</sub> SMALL S  C <sub>ob</sub> f <sub>T</sub>	Base-Emitter Saturation Voltage  SIGNAL CHARACTERISTICS  Output Capacitance  Current Gain - Bandwidth Product  Small-Signal Current Gain	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 10 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ kHz} \end{split}$		0.5 1.0 1.0 6.0 400	V V V
V <sub>BE(Sat)</sub> SMALL S  C <sub>ob</sub> f <sub>T</sub>	Base-Emitter Saturation Voltage  SIGNAL CHARACTERISTICS  Output Capacitance  Current Gain - Bandwidth Product	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 10 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ \end{split}$		0.5 1.0 1.0 6.0 400	V V V

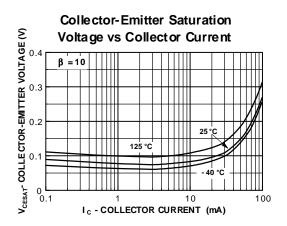
<sup>\*</sup>Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 2.0%

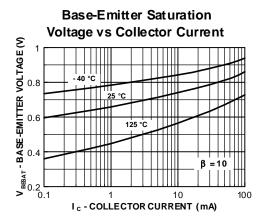
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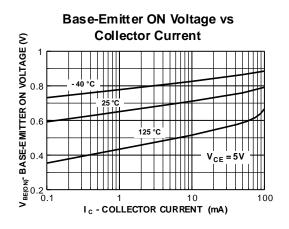
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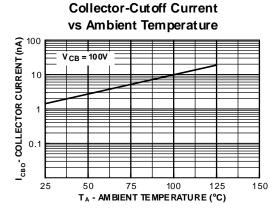
## **Typical Characteristics**

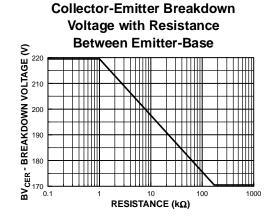








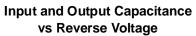


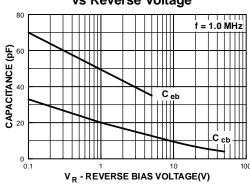


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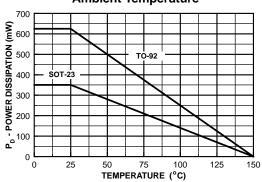
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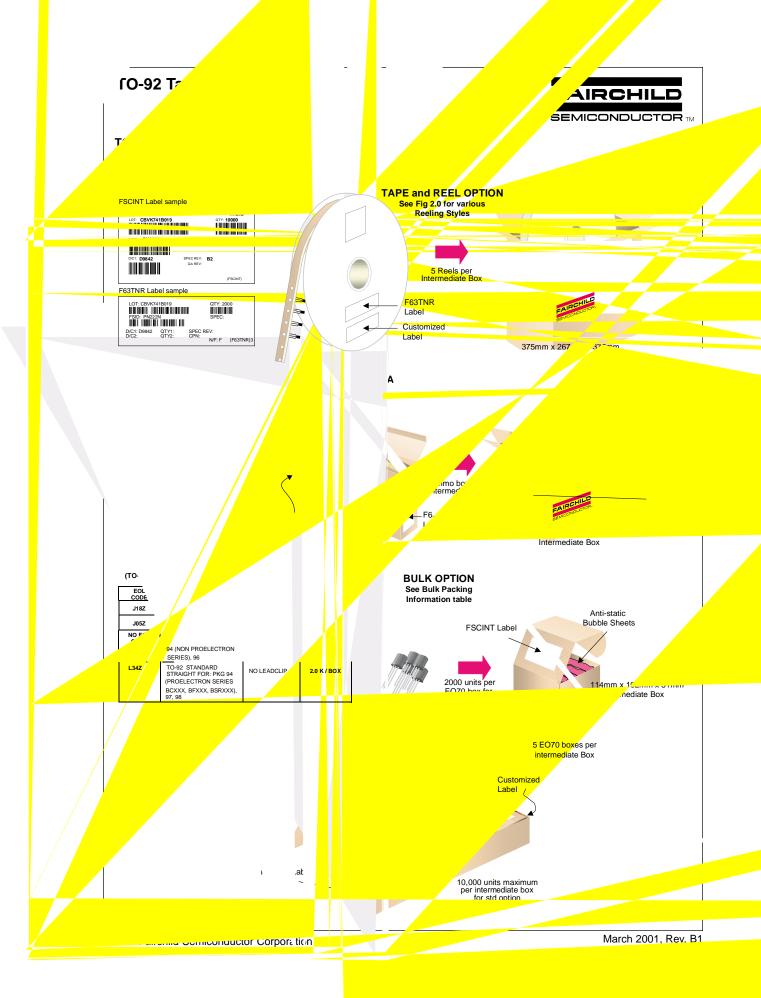
## **Typical Characteristics** (continued)

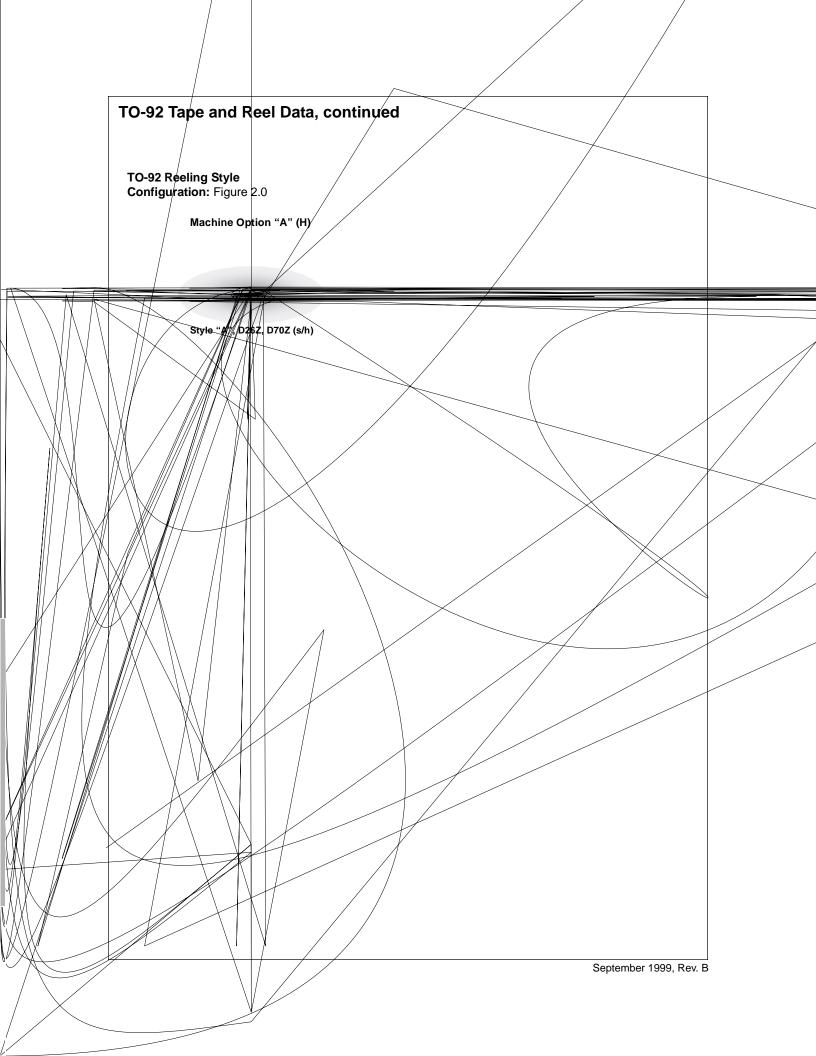


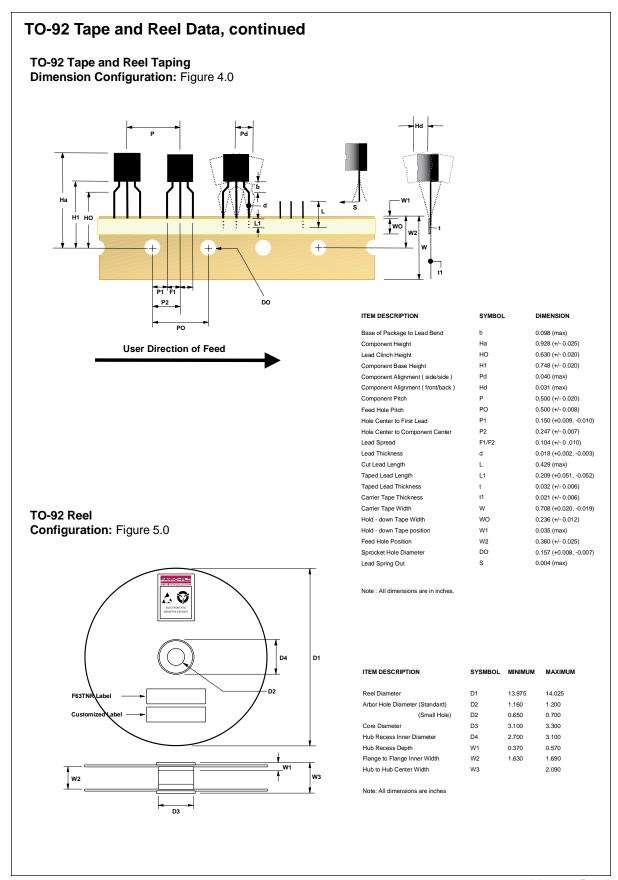


#### Power Dissipation vs Ambient Temperature





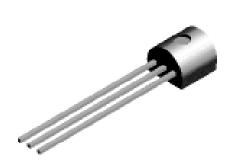


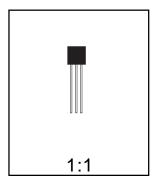


## **TO-92 Package Dimensions**



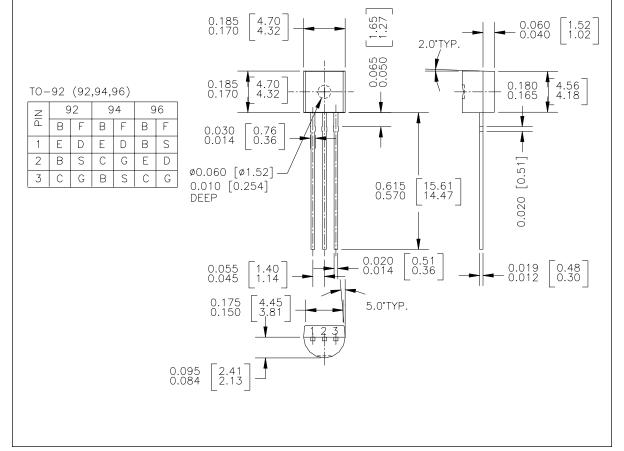
# TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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